

MITSUBISHI LASER DIODES
ML7xx16 SERIES
 2.5Gbps InGaAsP DFB LASER DIODE

**TYPE
NAME**

ML725B16F/ML720J16S/ML725J16F

DESCRIPTION

ML7xx16 series are uncooled DFB (Distributed Feedback) laser diodes for 2.5Gbps transmission emitting light beam at 1310nm. $\lambda/4$ shifted grating structure is employed to obtain excellent SMSR performance under 2.5Gbps modulation. Furthermore, ML7xx16 can operate in the wide temperature range from -20°C to 85°C without any temperature control.

FEATURES

- $\lambda/4$ phase shifted grating structure
- Wide temperature range operation (-20°C to 85°C)
- High side-mode-suppression-ratio (typical 45dB)
- High resonance frequency (typical 11GHz)

APPLICATION

2.5Gbps transmission

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Conditions	Ratings	Unit
Po	Output power	CW	6	mW
IF	Laser forward current	-	200	mA
VRL	Laser reverse voltage	-	2	V
IRD	PD forward current	-	2	mA
VRD	PD reverse voltage	-	20	V
Tc	Operation temperature	-	$-20 \sim +85$	$^{\circ}\text{C}$
Tstg	Storage temperature	-	$-40 \sim +100$	$^{\circ}\text{C}$

ELECTRICAL/OPTICAL CHARACTERISTICS (Tc=25°C)


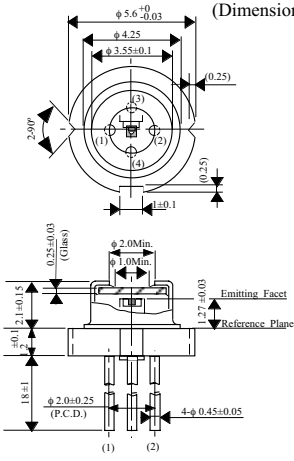
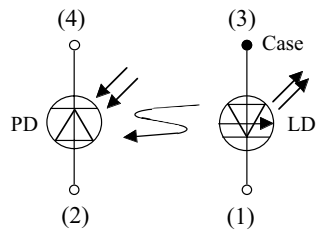
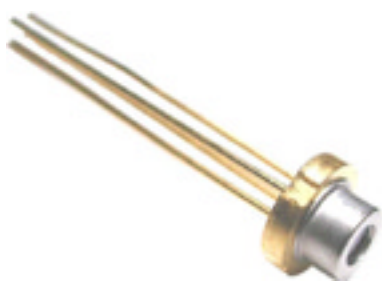
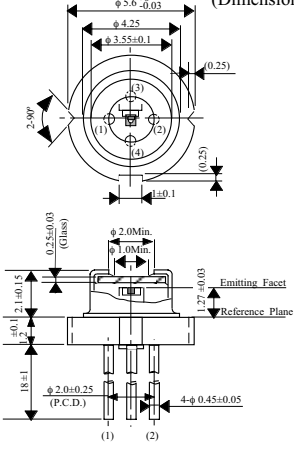
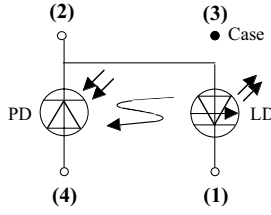
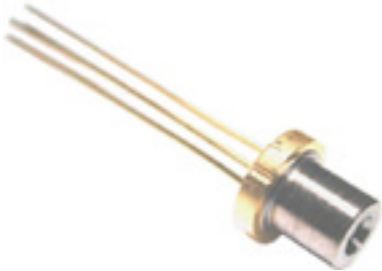
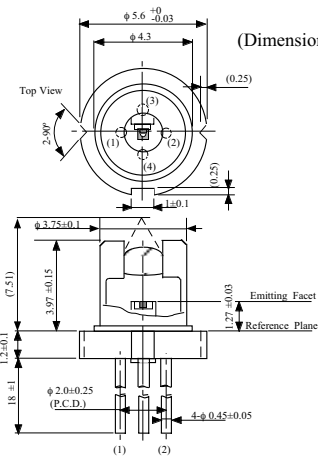
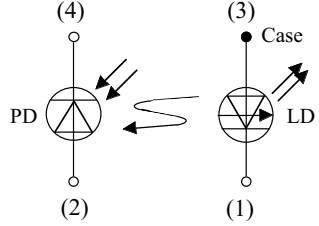
Symbol	Parameter	Conditions	Limits			Unit
			Min.	Typ.	Max.	
Ith	Threshold current	CW	-	10	15	mA
		CW, Tc=85°C	-	35	50	mA
Iop	Operation current	CW, Po=5mW	-	30	40	mA
		CW, Po=5mW, Tc=85°C	-	75	100	mA
Vop	Operating voltage	CW, Po=5mW	-	1.1	1.8	V
η	Slope efficiency	CW, Po=5mW	0.18	0.25	-	mW/mA
λ_p	Peak wavelength	CW, Po=5mW, Tc= $-20^{\circ}\text{C} \sim +85^{\circ}\text{C}$	1290	1310	1330	nm
SMSR	Side mode suppression ratio	CW, Po=5mW, Tc= $-20^{\circ}\text{C} \sim +85^{\circ}\text{C}$	35	45	-	dB
$\theta_{//}$	Beam divergence angle (parallel)	CW, Po=5mW	-	25	40	deg.
θ_{\perp}	(perpendicular)	CW, Po=5mW	-	30	47	deg.
fr	Resonance frequency	2.48832Gbps, I _{bias} =I _{th} , I _{pp} =40mA	-	11	-	GHz
tr,tf	Rise and fall time(10%-90%)	2.48832Gbps, I _{bias} =I _{th} , I _{pp} =40mA not including package	-	100	150	psec
Im	Monitoring current (PD)	CW, Po=5mW, VRD=1V	0.1	-	2.0	mA
Id	Dark current (PD)	VRD=5V	-	-	0.1	μA
Ct	Capacitance (PD)	VRD=5V, f=1MHz	-	10	20	pF



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OUTLINE DRAWINGS

<p>ML725B16F</p> 	<p>(Dimension:mm)</p> 	 <p>ML725B16F</p>
<p>ML720J16S</p> 	<p>(Dimension:mm)</p> 	 <p>ML720J16S</p>
<p>ML725J16F</p> 	<p>(Dimension:mm)</p> 	 <p>ML725J16F</p>

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TYPICAL CHARACTERISTICS

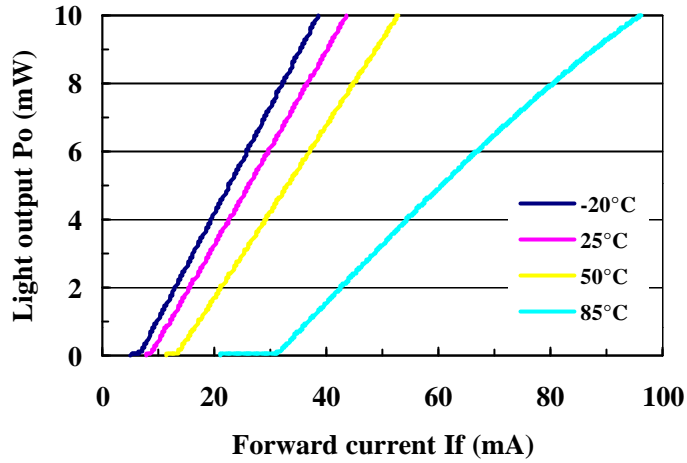


Fig. 1 Light output v.s. forward current

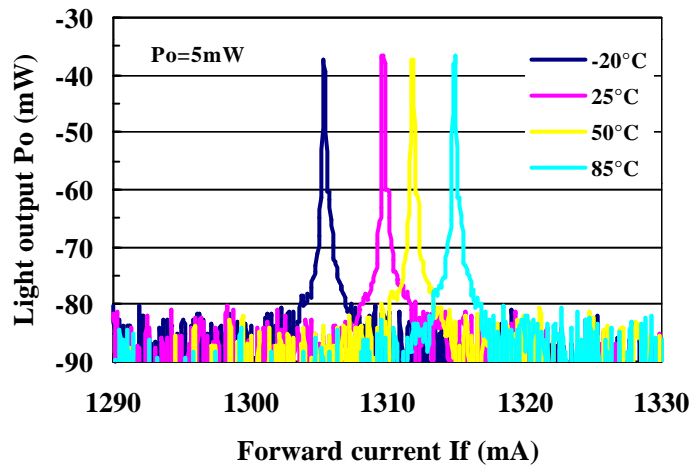


Fig. 2 Spectrum

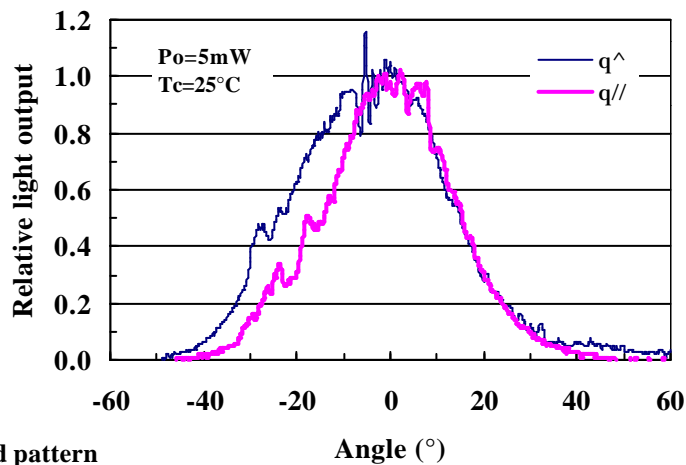


Fig. 3 Far field pattern